

GBJ20005 - GBJ2010

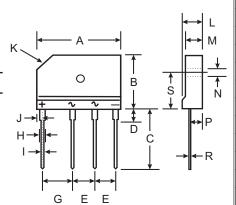
20A GLASS PASSIVATED BRIDGE RECTIFIER

Features

- Glass Passivated Die Construction
- High Case Dielectric Strength of 1500V_{RMS}
- Low Reverse Leakage Current
- Surge Overload Rating to 240A Peak
- Ideal for Printed Circuit Board Applications
- **UL Listed Under Recognized Component** Index, File Number E94661
- Lead Free Finish/RoHS Compliant (Note 4)

Mechanical Data

- Case: GBJ
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Plated Leads, Solderable per MIL-STD-202, Method 208 (e3)
- Lead Free Plating (Tin Finish).
- Polarity: Molded on Body
- Mounting: Through Hole for #6 Screw
- Mounting Torque: 5.0 in-lbs Maximum
- Marking: Type Number
- Weight: 6.6 grams (approximate)



GBJ						
Dim	Min	Max				
Α	29.70	30.30				
В	19.70	20.30				
С	17.00	18.00				
D	3.80	4.20				
E	7.30	7.70				
G	9.80	10.20				
Н	2.00	2.40				
I	0.90	1.10				
J	2.30	2.70				
K	3.0 \	3.0 X 45°				
L	4.40	4.80				
M	3.40	3.80				
N	3.10	3.40				
Р	2.50	2.90				
R	0.60	0.80				
S	10.80	11.20				
All Dimensions in mm						

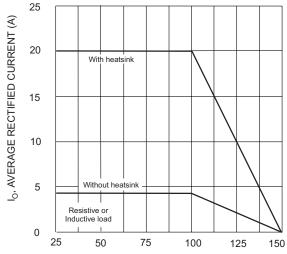
Maximum Ratings and Electrical Characteristics @ TA = 25°C unless otherwise specified

Single phase, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

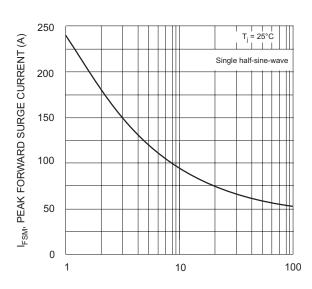
Characteristic	Symbol	GBJ 20005	GBJ 2001	GBJ 2002	GBJ 2004	GBJ 2006	GBJ 2008	GBJ 2010	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	50	100	200	400	600	800	1000	\ \
RMS Reverse Voltage	V _{R(RMS)}	35	70	140	280	420	560	700	V
Average Forward Rectified Output Current @ T _C = 110°C		20						Α	
Non-Repetitive Peak Forward Surge Current, 8.3 ms single half-sine-wave superimposed on rated load		240					Α		
Forward Voltage per element @ I _F = 10A	V _{FM}				1.05				V
$ \begin{array}{llllllllllllllllllllllllllllllllllll$		10 500					μΑ		
I ² t Rating for Fusing (t < 8.3 ms) (Note 1)		240					A ² s		
Typical Total Capacitance per Element (Note 2)		60					pF		
Typical Thermal Resistance Junction to Case (Note 3)		0.8					°C/W		
Operating and Storage Temperature Range		-55 to +150				°C			

- 1. Non-repetitive, for t > 1ms and < 8.3 ms.
- 2. Measured at 1.0 MHz and applied reverse voltage of 4.0V DC.
- 3. Unit mounted on 300 x 300 x 1.6mm Cu plate heat sink.
- 4. RoHS revision 13.2.2003. Glass and High Temperature Solder Exemptions Applied, see EU Directive Annex Notes 5 and 7.

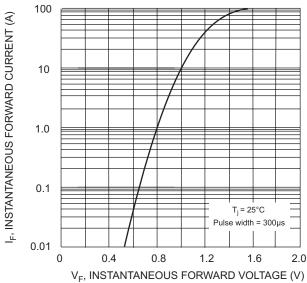




T_C, CASE TEMPERATURE (°C) Fig. 1 Forward Current Derating Curve



NUMBER OF CYCLES AT 60 Hz Fig. 3 Maximum Non-Repetitive Surge Current



V_F, INSTANTANEOUS FORWARD VOLTAGE (V) Fig. 2 Typical Forward Characteristics (per element)

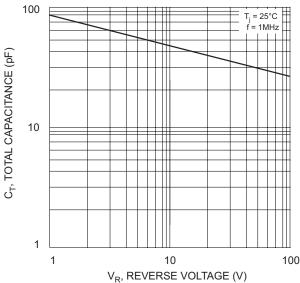
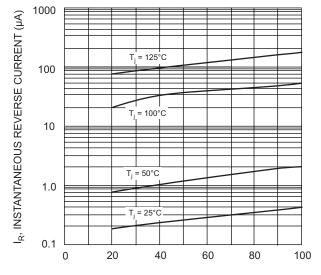


Fig. 4 Typical Total Capacitance, Per Element



PERCENT OF RATED PEAK REVERSE VOLTAGE (%) Fig. 5 Typical Reverse Characteristics



Ordering Information (Note 5)

Device	Packaging	Shipping		
GBJ20005-F	GBJ	15/Tube		
GBJ2001-F	GBJ	15/Tube		
GBJ2002-F	GBJ	15/Tube		
GBJ2004-F	GBJ	15/Tube		
GBJ2006-F	GBJ	15/Tube		
GBJ2008-F	GBJ	15/Tube		
GBJ2010-F	GBJ	15/Tube		

 $Notes: \quad 5. \quad \text{For packaging details, visit our website at http://www.diodes.com/datasheets/ap2008.pdf.}$

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